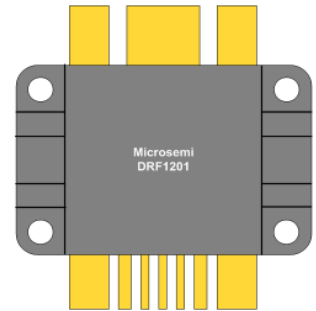
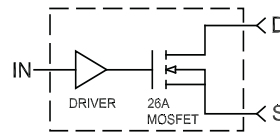



MOSFET Driver Hybrid

The DRF1201 hybrid includes a high power gate driver and the power MOSFET. The driver output can be configured as Inverting and Non-Inverting. It was designed to provide the system designer increased flexibility and lowered cost over a non-integrated solution.



FEATURES

- Switching Frequency: DC TO 30MHz
- Low Pulse Width Distortion
- Single Power Supply
- 1V CMOS Schmitt Trigger Input 1V Hysteresis
- Inverting Non-Inverting Select
- RoHS Compliant 
- Switching Speed 3-4ns
- $B_{V_{ds}} = 1Kv$
- $I_{ds} = 26A$ avg.
- $R_{ds(on)} \leq .55$ Ohm
- $P_D = 1100W$

TYPICAL APPLICATIONS

- Class C, D and E RF Generators
- Switch Mode Power Amplifiers
- Pulse Generators
- Ultrasound Transducer Drivers
- Acoustic Optical Modulators

Driver Absolute Maximum Ratings

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------------|-----------------------|-----|-----|-------------|------|
| V_{DD} | Supply Voltage | | | 15 | V |
| IN, FN | Input Single Voltages | | | -.7 to +5.5 | |
| $I_{O_{PK}}$ | Output Current Peak | | | 8 | A |
| T_{JMAX} | Operating Temperature | | | 175 | °C |

Driver Specifications

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------------|--|-----|-----|-----|------|
| V_{DD} | Supply Voltage | 10 | | 15 | V |
| IN | Input Voltage | 3 | | 5.5 | |
| $IN_{(R)}$ | Input Voltage Rising Edge | | 3 | | ns |
| $IN_{(F)}$ | Input Voltage Falling Edge | | 3 | | |
| I_{DDQ} | Quiescent Current | | 2 | | mA |
| I_O | Output Current | | 8 | | A |
| C_{ISS} | Input Capacitance | | 3 | | |
| R_{IN} | Input Parallel Resistance | | 1 | | MΩ |
| $V_{T(ON)}$ | Input, Low to High Out (See Truth Table) | 0.8 | | 1.1 | V |
| $V_{T(OFF)}$ | Input, High to Low Out (See Truth Table) | 1.9 | | 2.2 | |
| T_{DLY} | Time Delay (throughput) | | 38 | | ns |
| t_r | Rise Time | | 5 | | |
| t_f | Fall Time | | 5 | | |
| T_D | Prop. Delay | | 35 | | |

Driver Output Characteristics

DRF1201

| Symbol | Parameter | Min | Typ | Max | Unit |
|-----------|---|-----|------|-----|----------|
| C_{out} | Output Capacitance | | 2500 | | pF |
| R_{out} | Output Resistance | | .8 | | Ω |
| L_{out} | Output Inductance | | 3 | | nH |
| F_{MAX} | Operating Frequency CL = 3000nF + 50 Ω | 30 | | | MHz |
| F_{MAX} | Operating Frequency RL = 50 Ω | 50 | | | |

Driver Thermal Characteristics

| Symbol | Parameter | Min | Typ | Max | Unit |
|------------------|---|-----|------------|-----|-----------------------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case | | 1.5 | | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JHS}$ | Thermal Resistance Junction to Heat Sink | | 2.5 | | |
| T_{JSTG} | Storage Temperature | | -55 to 150 | | $^{\circ}\text{C}$ |
| P_{DJHS} | Maximum Power Dissipation @ $T_{SINK} = 25^{\circ}\text{C}$ | | 60 | | W |
| P_{DJC} | Total Power Dissipation @ $T_C = 25^{\circ}\text{C}$ | | 100 | | |

MOSFET Absolute Maximum Ratings

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------------|--|------|------|-----|--------------------|
| BV_{DSS} | Drain Source Voltage | 1000 | | | V |
| I_D | Continuous Drain Current $T_{HS} = 25^{\circ}\text{C}$ | | | 26 | A |
| $R_{DS(on)}$ | Drain-Source On State Resistance | | 0.55 | | Ω |
| T_{jmax} | Operating Temperature | | | 175 | $^{\circ}\text{C}$ |

MOSFET Dynamic Characteristics

| Symbol | Parameter | Min | Typ | Max | Unit |
|-----------|------------------------------|-----|------|-----|------|
| C_{iss} | Input Capacitance | | 2000 | | pF |
| C_{oss} | Output Capacitance | | 165 | | |
| C_{rss} | Reverse Transfer Capacitance | | 75 | | |

MOSFET Thermal Characteristics

| Symbol | Parameter | Min | Typ | Max | Unit |
|------------------|---|-----|------------|-----|-----------------------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case | | 0.53 | | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JHS}$ | Thermal Resistance Junction to Heat Sink | | 0.141 | | |
| T_{JSTG} | Storage Temperature | | -55 to 150 | | $^{\circ}\text{C}$ |
| P_{DHS} | Maximum Power Dissipation @ $T_{SINK} = 25^{\circ}\text{C}$ | | 1060 | | W |
| P_{DC} | Total Power Dissipation @ $T_C = 25^{\circ}\text{C}$ | | 2830 | | |

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

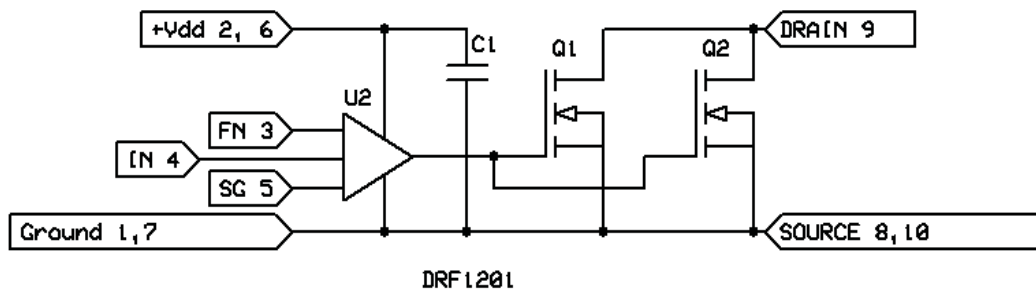


Figure 1, DRF1201 Simplified Circuit Diagram

The Simplified DRF1201 Circuit Diagram is illustrated above. By including the driver high speed by-pass capacitor (C1), the contribution to the internal parasitic loop inductance of the driver output is greatly reduced. This, coupled with the tight geometry of the hybrid, allows optimal gate drive to the MOSFET. This low parasitic approach, coupled with the Schmitt trigger input (IN), Kelvin signal ground (SG) and the Anti-Ring Function, provide improved stability and control in Kilowatt to Multi-Kilowatt, high Frequency applications. Both the FN and IN pins are referenced to the Kelvin ground (SG.) The signal is then applied to the intermediate drivers and level shifters; this section contains proprietary circuitry designed specifically for the ring abatement. The power drivers provide high current to the gate of the MOSFETS.

The Function (FN, pin 3) is the invert or non-invert select Pin, it is Internally held high.

| Truth Table *Referenced to SG | | |
|-------------------------------|-------------|--------|
| FN (pin 3)* | IN (pin 4)* | MOSFET |
| HIGH | HIGH | ON |
| HIGH | LOW | OFF |
| LOW | HIGH | OFF |
| LOW | LOW | ON |

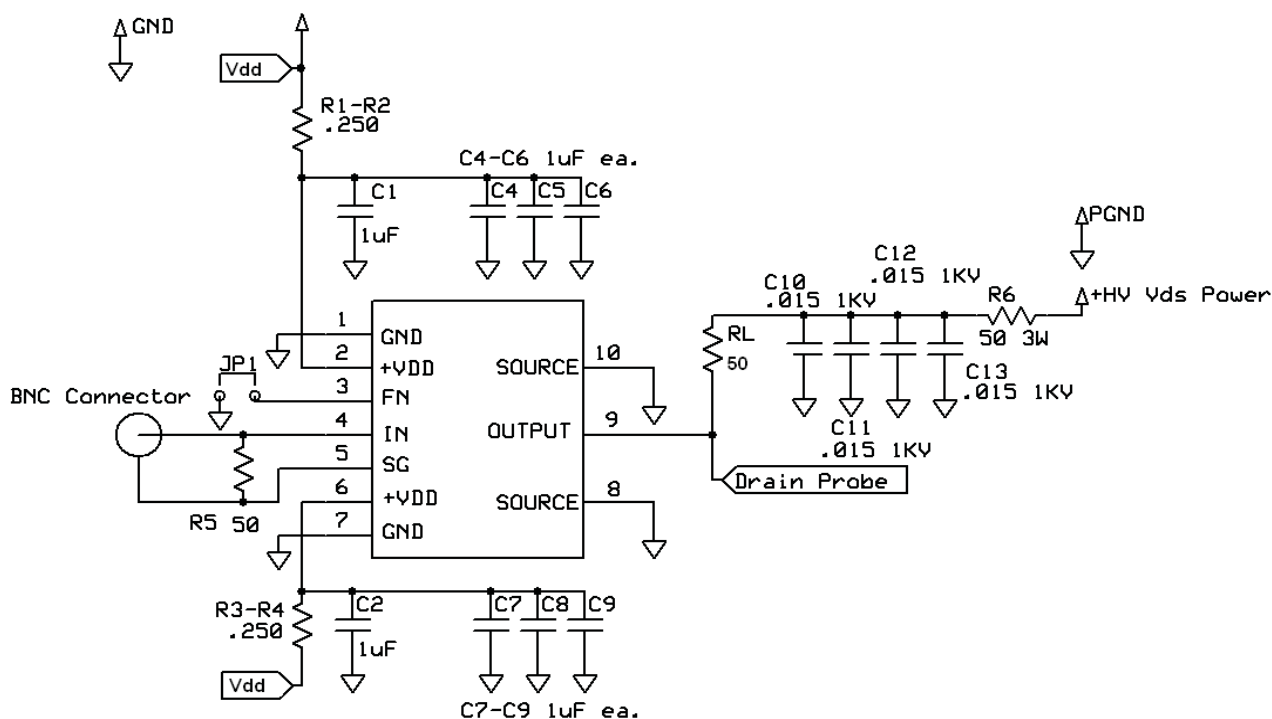
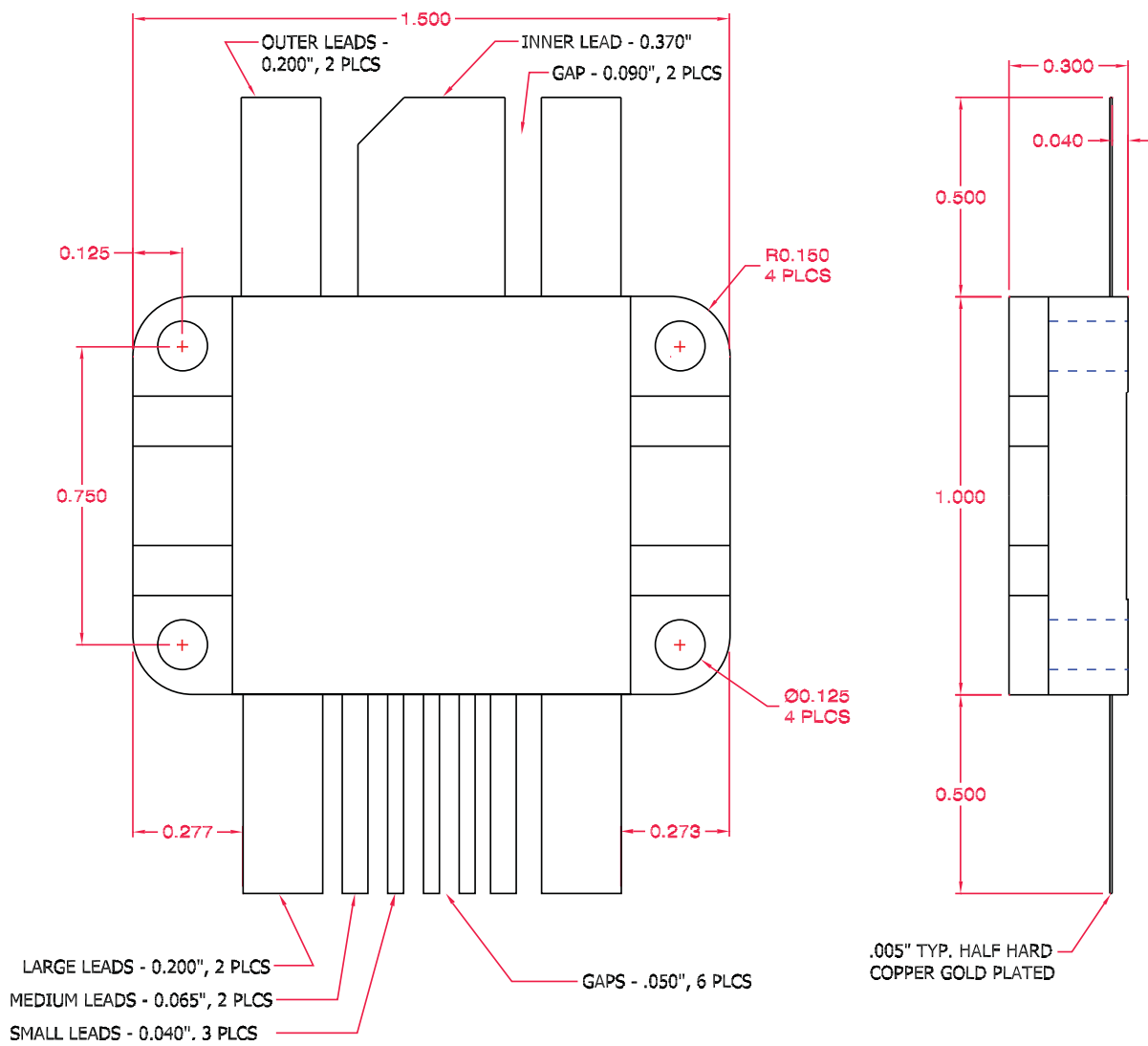


Figure 2, DRF1201 Test Circuit

The Test Circuit illustrated above was used to evaluate the DRF1201 (available as an evaluation Board DRF12XX / EVALSW.) The input control signal is applied to the DRF1201 via IN(4) and SG(5) pins using RG188. This provides excellent noise immunity and control of the signal ground currents.

The +V_{DD} inputs (2,6) are by-passed (C1, C2, C4-C9), this is in addition to the internal by-passing mentioned previously. The capacitors used for this function must be capable of supporting the RMS currents and frequency of the gate load. R_L set for I_{DM} at V_{DS} max this load is used to evaluate the output performance of the DRF1201.

| Pin Assignments | |
|-----------------|--------|
| Pin 1 | Ground |
| Pin 2 | +Vdd |
| Pin 3 | FN |
| Pin 4 | IN |
| Pin 5 | SG |
| Pin 6 | +Vdd |
| Pin 7 | Ground |
| Pin 8 | Source |
| Pin 9 | Drain |
| Pin 10 | Source |



All dimensions are ± .005

Figure 3, DRF1201 Mechanical Outline



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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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